L Number		Search Text	DB	Time stamp
3	69	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	USPAT;	2002/04/22 09:19
		Gan) or (III-V adj nitride))	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	60	1	USPAT;	2002/04/18 11:36
•		nitride and (anneal\$3 or PTP or RTA or	US-PGPUB;	
		(rapid adj thermal) or (heat adj treat\$4))	EPO; JPO;	
			DERWENT; IBM TDB	
_	29	"hole density" and nitride and (anneal\$3	USPAT;	2002/04/18 11:39
		or PTP or RTA or (rapid adj thermal) or	US-PGPUB;	2000,00,20
		(heat adj treat\$4)) and "p-type"	EPO; JPO;	
			DERWENT;	
	100	40, 2	IBM_TDB	0000/04/10 11 40
-	182	("hole density" or "carrier density") and nitride and (anneal\$3 or PTP or RTA or	USPAT; US-PGPUB;	2002/04/18 11:42
		(rapid adj thermal) or (heat adj treat\$4))	EPO; JPO;	
•		and "p-type"	DERWENT;	
			IBM TDB	
-	48		USPAT;	2002/04/18 11:47
		nitride and (anneal\$3 or PTP or RTA or	US-PGPUB;	
		(rapid adj thermal) or (heat adj treat\$4))	EPO; JPO;	
		and "p-type" and "III-V"	DERWENT; IBM TDB	
_	186	(("hole density" or "carrier density" or	USPAT;	2002/04/18 11:51
		resist\$4) same (anneal\$3 or PTP or RTA or	US-PGPUB;	
		(rapid adj thermal) or (heat adj	EPO; JPO;	
	*.	treat\$4))) and "p-type" and "III-V" and	DERWENT;	
	110	nitride	IBM_TDB	2002/04/19 11.52
-	119	(("hole density" or "carrier density" or resist\$4) same (anneal\$3 or PTP or RTA or	USPAT; US-PGPUB;	2002/04/18 11:53
		(rapid adj thermal) or (heat adj	EPO; JPO;	
		treat\$4))) and "p-type" and "III-V" and	DERWENT;	
		nitride and hydrogen	IBM_TDB	
-	103		USPAT;	2002/04/18 14:35
		resist\$4) same (anneal\$3 or PTP or RTA or	US-PGPUB;	
		(rapid adj thermal) or (heat adj treat\$4))) and "p-type" and "III-V" and	EPO; JPO; DERWENT;	
		nitride and hydrogen and grow\$3	IBM TDB	
<u>-</u>	101	1	USPAT;	2002/04/18 14:47
		(resistance or resistivity))) same	US-PGPUB;	
		((anneal or annealed or annealing) or PTP	EPO; JPO;	
		or RTA or (rapid adj thermal) or (heat adj	DERWENT;	
		<pre>(treat or treated or treating or treatment))) and "p-type" and "III-V" and</pre>	IBM_TDB	*
		nitride and hydrogen and grow\$3		A Li
-	109	(("hole density" or "carrier density" or	USPAT;	2002/04/18 14:52
		(resistance or resistivity))) same	US-PGPUB;	
		((anneal or annealed or annealing) or PTP	EPO; JPO;	
		or RTA or (rapid adj thermal) or (heat adj (treat or treated or treating or	DERWENT; IBM TDB	
•		treat or treated or treating of treatment))) and "p-type" and "III-V" and	1551_155	
		nitride and hydrogen		
-	136	(("hole density" or "carrier density" or	USPAT;	2002/04/18 17:10
		(resistance or resistivity))) same	US-PGPUB;	
		((anneal or annealed or annealing) or PTP	EPO; JPO;	
		or RTA or (rapid adj thermal) or (heat adj (treat or treated or treating or	DERWENT; IBM TDB	
		(treat or treated or treating or   treatment))) and (p-type adj GaN)	1511-158	
_	14		USPAT;	2002/04/18 15:04
			US-PGPUB;	
			EPO; JPO;	
		·	DERWENT;	
		07/070 145 71 20	IBM_TDB   USPAT;	2002/04/18 15:04
_	0	07/970,145.rlan.	US-PGPUB;	2002/04/10 13.04
	1		EPO; JPO;	
		3	I DEC, OLG,	
			DERWENT;	

-	2	970,145.ap.	USPAT;	2002/04/18 15:04
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
l _	92	(("hole density" or "carrier density" or	USPAT;	2002/04/18 17:13
	"	(resistance or resistivity))) same	US-PGPUB;	2002/04/18 17:13
		((anneal or annealed or annealing) or PTP	EPO; JPO;	
		or RTA or (rapid adj thermal) or (heat adj	DERWENT;	
		(treat or treated or treating or	IBM TDB	
		treatment))) and (p-type adj GaN) and		
		(etch or etching or etchant)	ļ	
-	96	(("hole density" or "carrier density" or	USPAT;	2002/04/19 09:22
		(resistance or resistivity)) same (etch or	US-PGPUB;	
		etching or etchant or plasma)) and (p-type	EPO; JPO;	
		adj GaN)	DERWENT;	
İ	24	// // // / / / / / / / / / / / / / / /	IBM_TDB	0000 (04 (10 00 10
-	34		USPAT;	2002/04/19 09:19
		(resistance or resistivity)) same (etch or	US-PGPUB;	
		etching or etchant or plasma)) same (p-type adj GaN)	EPO; JPO; DERWENT;	
		(h clhe anl dan)	IBM TDB	
-	181	(etch or etching or etchant or plasma)	USPAT;	2002/04/19 13:28
		same (p-type adj GaN)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	96	(("hole density" or "carrier density" or	USPAT;	2002/04/19 09:20
		(resistance or resistivity)) same (etch or	US-PGPUB;	
1.		etching or etchant or plasma)) and(p-type	EPO; JPO;	
		adj GaN)	DERWENT; IBM TDB	
_	100	(("hole density" or "carrier density" or	USPAT;	2002/04/19 09:26
	100	(resistance or resistivity)) same (clean	US-PGPUB;	2002/04/13 03.20
		or cleaned or cleaning or koh or naoh or	EPO; JPO;	
		nh4oh etch or etching or etchant or	DERWENT;	
		plasma)) and (p-type adj GaN)	IBM_TDB	
-	22	(koh or naoh or nh4oh) and (p-type adj	USPAT;	2002/04/19 09:31
		GaN)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	314	(koh or naoh or nh4oh) and GaN	IBM_TDB USPAT;	2002/04/19 09:31
-	314	(Kon of haon of hindon) and dan	US-PGPUB;	2002/04/13 03:31
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	31	(koh or naoh or nh4oh) same GaN	USPĀT;	2002/04/19 10:16
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	0150	(CoN on /n time add CoN) on HITT VII an	IBM_TDB	2002/04/19 13:10
<del>-</del>	2159	(GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN)	USPAT; US-PGPUB;	2002/04/13 13:10
		same (etch or etching or etchant or Naoh	EPO; JPO;	
		or Koh)	DERWENT;	
		<del></del> /	IBM TDB	
_	146	(GaN or (p-type adj GaN) or "III-V" or	USPAT;	2002/04/19 11:04
		(gallium adj nitride) or AlInGan or AlGaN)	US-PGPUB;	
		same (etch or etching or etchant or Naoh	EPO; JPO;	
		or Koh) same (resistivity or resistance)	DERWENT;	
	_		IBM_TDB	2002/04/10 10-24
-	9	(com: (F -3f)	USPAT;	2002/04/19 10:34
.		(gallium adj nitride) or AlInGan or AlGaN) same (etch or etching or etchant or Naoh	US-PGPUB; EPO; JPO;	
		or Koh) same (resistivity or resistance)	DERWENT;	
		same hydrogen	IBM TDB	
_i		Jame Ilfatogen		

[-	412	(GaN or (p-type adj GaN) or "III-V" or	USPAT;	2002/04/19 10:35
Į		(gallium adj nitride) or AlInGan or AlGaN)	US-PGPUB;	
		same (passivation or passivating or	EPO; JPO; DERWENT;	
1		passivate)	IBM TDB	
	50	(GaN or (p-type adj GaN) or "III-V" or	USPAT;	2002/04/19 10:37
-	58	(gallium adj nitride) or AlInGan or AlGaN)	US-PGPUB;	2002,007,20
		same (passivation or passivating or	EPO; JPO;	
		passivate) same (hydrogen or h or h2)	DERWENT;	
1			IBM_TDB	
-	10	(GaN or (p-type adj GaN) or "III-V" or	USPAT;	2002/04/19 10:42
		(gallium adj nitride) or AlInGan or AlGaN)	US-PGPUB;	
	]	same (passivation or passivating or	EPO; JPO;	
		passivate) same (hydrogen or h or h2) same	DERWENT; IBM TDB	1
		(Etch or etchant or etching)	USPAT;	2002/04/19 10:43
-	4	(GaN or (p-type adj GaN) or "III-V" or (gallium adj nitride) or AlInGan or AlGaN)	US-PGPUB;	2002,01,20
	1	same ((hydrogen or H) adj remov\$3)	EPO; JPO;	
		Same (mydrogen or n, de) remains,	DERWENT;	
			IBM_TDB	
_	87	(GaN or (p-type adj GaN) or "III-V" or	USPAT;	2002/04/19 11:45
		(gallium adj nitride) or AlInGan or AlGaN)	US-PGPUB;	
		same (surface adj treat\$4)	EPO; JPO; DERWENT;	
		·	IBM TDB	
	0.5	con or "III-V adi	USPAT;	2002/04/19 11:47
-	25	(GaN or (p-type adj GaN) or "III-V adj nitride" or (gallium adj nitride) or	US-PGPUB;	
		AlinGan or AlGaN) same (surface adj	EPO; JPO;	
		treat\$4)	DERWENT;	
		· ·	IBM_TDB	
_	32	(GaN or (p-type adj GaN) or "III-V adj	USPAT;	2002/04/19 13:11
	1	nitride" or (gallium adj nitride) or	US-PGPUB;	
1		AlInGan or AlGaN) same (Naoh or Koh or	EPO; JPO; DERWENT;	
		nh4oh)	IBM TDB	
	6756	(etch or etching or etchant or plasma)	USPAT;	2002/04/19 13:29
-	6756	same resistivity	US-PGPUB;	
İ		Same resistivity	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/04/19 13:31
-	1016	(etch or etching or etchant or plasma)	USPAT; US-PGPUB;	2002/04/19 13.31
		same resistivity same (GaN or (p-type adj	EPO; JPO;	
		GaN) or "III-V" or nitride)	DERWENT;	
			IBM TDB	
_	. 33	(etch or etching or etchant or plasma)	USPAT;	2002/04/19 13:32
		same resistivity same ((p-type ad) GaN)	US-PGPUB;	
		or GaN or "III-V")	EPO; JPO;	
			DERWENT; IBM TDB	
		l	USPAT;	2002/04/19 13:36
-	58	(clean or cleaning or removing or hydrogen) same resistivity same ((p-type	US-PGPUB;	
		adj GaN) or GaN or "III-V")	EPO; JPO;	
		auj dan, of dan of the v	DERWENT;	
			IBM_TDB	
_	9	(clean or cleaning or removing) same	USPAT;	2002/04/19 13:48
1		resistivity same ((p-type adj GaN) or GaN	US-PGPUB;	
		or "III-V")	EPO; JPO;	
			DERWENT; IBM TDB	
		(chemical adj treatment) same resistivity	USPAT;	2002/04/19 13:48
-	1		US-PGPUB;	
		same ((p-type adj GaN) of GaN of 111-v)	EPO; JPO;	
			DERWENT;	
1.			IBM_TDB	2002/04/19 13:55
_	3554	clean and (GaN or p-GaN or "p-type GaN" or	USPAT;	2002/04/19 13:33
		"III-V nitride" or p-type)	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
1	1			

- 1	247	clean and (GaN or p-GaN or "p-type GaN" or	USPAT; US-PGPUB;	2002/04/19 13:58
		"III-V nitride" or p-type) and (koh or	EPO; JPO;	Ì
		naoh or nh4oh)	DERWENT;	İ
	l		IBM_TDB	222242420 14.15
_	20	clean same (GaN or p-GaN or "p-type GaN"	USPAT;	2002/04/19 14:15
		or "III-V nitride" or p-type) and (koh or	US-PGPUB; EPO; JPO;	
		naoh or nh4oh)	DERWENT;	
•			IBM TDB	
_	134	plasma same (GaN or p-GaN or "p-type GaN"	USPAT;	2002/04/19 17:27
_	13.	or "III-V nitride" or p-type) and (koh or	US-PGPUB; EPO; JPO;	
		naoh or nh4oh)	DERWENT;	
			IBM TDB	
	3	022,364.ap.	USPAT;	2002/04/19 14:22
_		022,304.45.	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	·
•		000 600 00	USPAT;	2002/04/19 14:23
_	3	020,629.ap.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		"	IBM_TDB USPAT;	2002/04/19 14:24
_	0	"Etching adj GaN" and "DC adj plasma"	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB USPAT;	2002/04/19 16:47
ļ <u>-</u>	641	ultrasonic\$3 and clean\$3 and (Gan or	US-PGPUB;	2002/04/13 10:1/
		(p-type adj Gan) or p-type)	EPO; JPO;	
1		•	DERWENT;	
			IBM_TDB	2002/04/19 16:47
_	108	ultrasonic\$3 and clean\$3 same (Gan or	USPAT; US-PGPUB;	2002/04/19 10.4/
		(p-type adj Gan) or p-type)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	32	ultrasonic\$3 same clean\$3 same (Gan or	USPAT;	2002/04/19 16:50
		(p-type adj Gan) or p-type)	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
	5	ultrasonic\$3 same clean\$3 same (Gan or	USPAT;	2002/04/19 16:51
_		(p-type adj Gan))	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
	16	ultrasonic\$3 same (Gan or (p-type adj	USPAT;	2002/04/19 16:52
-	16	(Gan))	US-PGPUB;	·
			EPO; JPO; DERWENT;	
			IBM TDB	
		ultrasonic\$3 same (Gan or (p-type adj Gan)	_	2002/04/19 16:52
-	563	or nitride)	05 101027	
		of mittide,	EPO; JPO;	
			DERWENT; IBM TDB	
		(Gan an Antumo adi Gan)		2002/04/22 09:18
-	16	ultrasonic\$3 same (Gan or (p-type adj Gan)	US-PGPUB;	
		or (III-V adj nitride))	EPO; JPO;	
			DERWENT;	
1.			IBM_TDB	2002/04/19 16:53
-	30		USPAT; US-PGPUB;	2002/01/12/20100
		or (III-V))	EPO; JPO;	
			DERWENT;	
1	ı	1	IBM TDB	1

or "III-V nitride" ) and (koh or naoh or nh4oh)	USPAT; 2002/04/19 17:28 US-PGPUB; EPO; JPO; DERWENT; IBM TDB
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